

## ABSTRACT OF THE DISCLOSURE

A semiconductor light emitting device includes:  
a silicon substrate; and a plurality of column-shaped  
5 multilayered structures formed on the silicon substrate  
in such a manner that the column-shaped multilayered  
structures are insulated from one another, the  
column-shaped multilayered structures being made of a  
nitride semiconductor material, and each column-shaped  
10 multilayered structure including a light emitting layer,  
wherein the column-shaped multilayered structures are  
connected to one another by an electrode.

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